



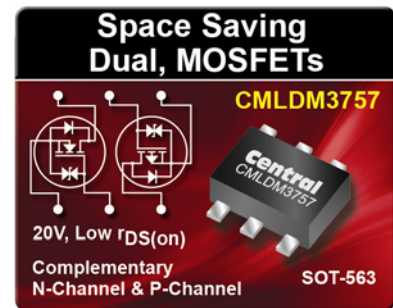
News Release

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For Immediate Release

Space saving N-Channel and P-Channel MOSFETs in the ultra miniature SOT-563 package



Hauppauge, NY USA – March 1, 2011 – Central Semiconductor Corp. announces the **CMLDM3757** dual, complementary N-Channel and P-Channel MOSFETs packaged in the ultra miniature SOT-563 surface mount case. Both devices have a maximum rated Drain-Source voltage of 20V, and a minimum Gate-Source threshold voltage of 450mV. The N-Channel device has a maximum continuous Drain current of 540mA with a low $r_{DS(ON)}$ of 550m Ω , while the P-Channel has a 430mA rating and a $r_{DS(ON)}$ of 900m Ω .

The CMLDM3757 is the ideal space saving solution for design engineers seeking complementary N-Channel and P-Channel energy efficient MOSFETs. The SOT-563 package uses a board space area of only 2.9 sq mm and has a maximum profile of 0.6mm. Designed to solve space constrained circuit layouts, this product is ideal for the latest portable electronic products such as cellular phones, MP3 players, Bluetooth headsets, blood glucose analyzers, and hearing aids. Applications for these devices include DC to DC conversion, load switching, battery charging, and overall power management.

Pricing starts at US\$0.14 each for 3,000 pieces on tape and reel. Sample devices are available upon request.

Central Semiconductor manufactures innovative discrete semiconductors to meet design engineers' ever changing challenges. Specifications for this device can be found in the New Products / Latest Updates section of Central's website at: www.centralsemi.com/product/whatsnew/newprod/

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